

IN THE CLAIMS:

Claims 16 through 21 were previously cancelled. Claims 1 and 3 through 15 have been amended herein. All of the pending claims are presented below. This listing of claims will replace all prior versions and listings of claims in the application. Please enter these claims as amended.

Listing of Claims:

1. (Currently amended) A semiconductor processing assembly, comprising:  
a reaction chamber configured to house at least one semiconductor substrate;  
a heater located at least partially within ~~said~~ the reaction chamber;  
at least one temperature sensor configured to sense a temperature and transmit a signal in response to a sensed temperature; and  
a temperature regulator in communication with ~~said~~ the heater and ~~said~~ the at least one temperature sensor and configured to continuously vary a thermal output of ~~said~~ the heater and a temperature of at least a portion of ~~said~~ the at least one semiconductor substrate responsive to ~~said~~ the signal.
2. (Original) The semiconductor processing assembly of claim 1, comprising a plurality of temperature sensors for sensing temperatures at a corresponding plurality of locations.
3. (Currently amended) The semiconductor processing assembly of claim 1, wherein ~~said~~ the at least one temperature sensor is configured to sense a temperature within ~~said~~ the reaction chamber.

4. (Currently amended) The semiconductor processing assembly of claim 1, wherein ~~said the~~ at least one temperature sensor is configured to sense a temperature of at least an area of ~~said the~~ at least one semiconductor substrate.

5. (Currently amended) The semiconductor processing assembly of claim 1, wherein ~~said the~~ temperature regulator is configured to vary ~~said the~~ thermal output of ~~said the~~ heater over a span of time.

6. (Currently amended) The semiconductor processing assembly of claim 1, wherein ~~said the~~ reaction chamber comprises at least one of a hot wall furnace and a cold wall furnace.

7. (Currently amended) The semiconductor processing assembly of claim 1, wherein ~~said the~~ reaction chamber comprises at least one of a vertical furnace and a horizontal furnace.

8. (Currently amended) The semiconductor processing assembly of claim 1, wherein ~~said the~~ reaction chamber is configured to house only a single semiconductor substrate at a time.

9. (Currently amended) The semiconductor processing assembly of claim 1, wherein ~~said the~~ reaction chamber comprises a plasma enhanced chamber.

10. (Currently amended) The semiconductor processing assembly of claim 1, wherein ~~said the~~ reaction chamber comprises at least one of a high-pressure chamber, a low-pressure chamber, and an atmospheric-pressure chamber.

11. (Currently amended) The semiconductor processing assembly of claim 1, wherein ~~said the~~ reaction chamber comprises at least one of a furnace and a rapid thermal processing chamber.

12. (Currently amended) The semiconductor processing assembly of claim 1, further comprising a rotator within-~~said- the~~ reaction chamber.

13. (Currently amended) The semiconductor processing assembly of claim 12, wherein-~~said- the~~ rotator is configured to rotate-~~said- the~~ at least one semiconductor substrate.

14. (Currently amended) A supplement to a fabrication chamber configured to perform a deposition process on a substrate, ~~said- the~~ supplement comprising:  
a variable substrate temperature generation system configured to operate in cooperation with initiation of-~~said- the~~ deposition process, ~~said- the~~ variable substrate temperature generation system comprising a feedback control system in communication with at least one temperature sensor and a heating element of-~~said- the~~ fabrication chamber, ~~said- the~~ feedback control system configured to cause-~~said- the~~ heating element of-~~said- the~~ fabrication chamber to continuously alter a thermal output within-~~said- the~~ fabrication chamber and a temperature of at least a portion of the substrate in response to transmission of a signal from-~~said- the~~ at least one temperature sensor.

15. (Currently amended) The supplement of claim 14, wherein-~~said- the~~ feedback control system is configured to receive-~~said- the~~ signal and to alter power provided to-~~said- the~~ heating element in response to-~~said- the~~ signal.

16.-21. (Cancelled)